



## SSCJ56N650GTF

N-Channel 650V Super Junction Power MOSFET

### ➤ Features

| $V_{DS}$ | $R_{DS(ON)}$ Typ. | $I_D$ |
|----------|-------------------|-------|
| 650V     | 56mΩ@10V          | 55A   |

### ➤ Description

- Low ON Resistance
- Improved dv/dt Capability
- Intrinsic Fast-Recovery Body Diode
- Fast switching capability
- 100% Avalanche Tested
- RoHS compliant

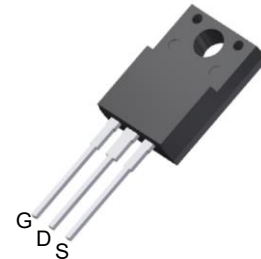
### ➤ Applications

- EV Charger
- Server/Telecom/PC Power
- AC-DC Power Management
- Solar Inverte

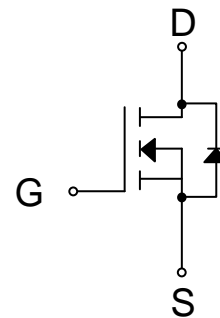
### ➤ Ordering Information

| Device        | Package   | Shipping |
|---------------|-----------|----------|
| SSCJ56N650GTF | TO220F-3L | 50/Tube  |

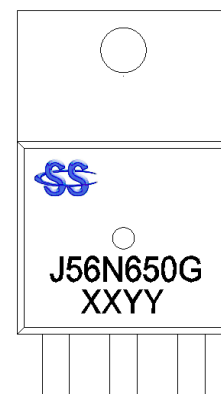
### ➤ Pin Configuration



TO220F-3L (Top View)



Pin Configuration



### Marking

(XXYY: Internal Traceability Code)



➤ **Absolute Maximum Ratings ( $T_J=25^{\circ}\text{C}$  unless otherwise noted)**

| Symbol        | Parameter   | Ratings    | Unit               |
|---------------|---|------------|--------------------|
| $V_{DS}$      | Drain-to-Source Voltage                               | 650        | V                  |
| $V_{GS}$      | Gate-to-Source Voltage (dynamic)                      | $\pm 30$   |                    |
| $I_D$         | Continuous Drain Current $T_J=25^{\circ}\text{C}$     | 55         | A                  |
| $I_{DM}$      | Pulsed Drain Current                                  | 165        | A                  |
| dv/dt         | MOSFET dv/dt Ruggedness( $V_{DS}=0\sim 480\text{V}$ ) | 50         | V/ns               |
| $T_{STG}/T_J$ | Junction & Storage Temperature Range                  | -55 to 150 | $^{\circ}\text{C}$ |

➤ **Thermal Resistance Ratings ( $T_J=25^{\circ}\text{C}$  unless otherwise noted)**

| Symbol          | Parameter  | Ratings | Unit                        |
|-----------------|--|---------|-----------------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient <sup>c</sup> | 66      | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case                 | 3.0     |                             |



➤ **Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

| Parameter                             | Symbol               | Test Conditions   | Min. | Typ. | Max. | Unit |
|---------------------------------------|----------------------|---|------|------|------|------|
| Drain-Source Breakdown Voltage        | V <sub>(BR)DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA  | 650  |      |      | V    |
| Zero Gate Voltage Drain Current       | I <sub>DSS</sub>     | V <sub>DS</sub> = 650V, V <sub>GS</sub> = 0V  |      |      | 10   | μA   |
| Gate-Source Leak Current              | I <sub>GSS</sub>     | V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V  |      |      | ±100 | nA   |
| Gate Threshold Voltage                | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA  | 3    | 4    | 5    | V    |
| Drain-Source On-Resistance            | R <sub>DS(on)</sub>  | V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A   |      | 56   | 68   | mΩ   |
| Input Capacitance                     | C <sub>ISS</sub>     | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V,<br>f = 1MHz  |      | 4528 |      | pF   |
| Output Capacitance                    | C <sub>OSS</sub>     |   |      | 414  |      |      |
| Reverse Transfer Capacitance          | C <sub>RSS</sub>     |   |      | 3    |      |      |
| Total Gate Charge                     | Q <sub>G</sub>       | V <sub>GS</sub> = 0 to 10V, V <sub>DS</sub> = 400V,<br>I <sub>D</sub> = 17.1A                   |      | 94   |      | nC   |
| Gate to Source Charge                 | Q <sub>GS</sub>      |   |      | 25   |      |      |
| Gate to Drain Charge                  | Q <sub>GD</sub>      |   |      | 35   |      |      |
| Turn-on Delay Time                    | T <sub>D(ON)</sub>   | V <sub>GS</sub> = 13V, V <sub>DS</sub> = 400V,<br>I <sub>D</sub> = 17.1A, R <sub>G</sub> = 5.3Ω |      | 22   |      | ns   |
| Rise Time                             | T <sub>r</sub>       |   |      | 11   |      |      |
| Turn-off Delay Time                   | T <sub>D(OFF)</sub>  |   |      | 87   |      |      |
| Fall Time                             | T <sub>f</sub>       |   |      | 9    |      |      |
| Drain to Source Diode Forward Voltage | V <sub>SD</sub>      | V <sub>GS</sub> = 0V  |      | 0.88 | 1.2  | V    |



➤ Typical Performance Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

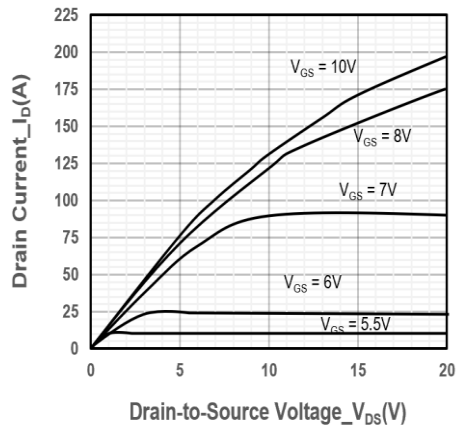


Figure 1: Output Characteristics

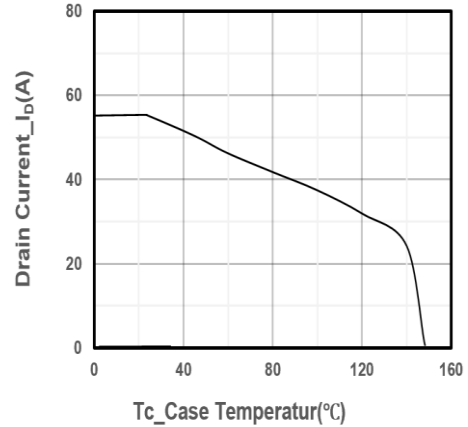


Figure 2: Drain current De-rating

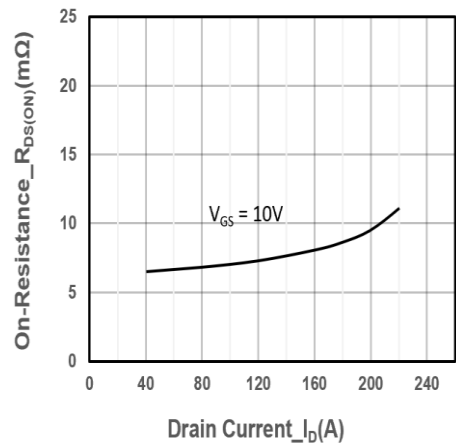


Figure 3:  $R_{DS(ON)}$  vs Drain Current

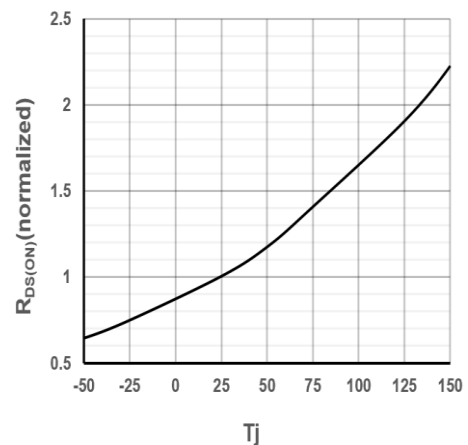


Figure 4:  $R_{DS(ON)}$  vs junction temperature

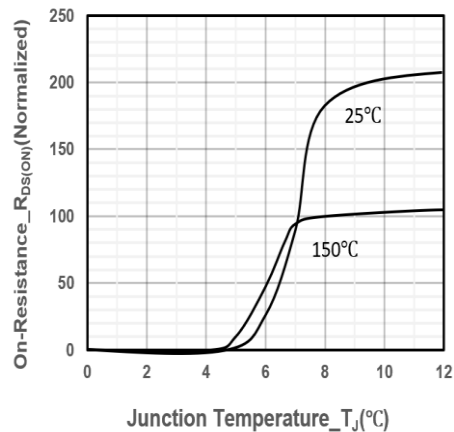


Figure 5: Transfer characteristics

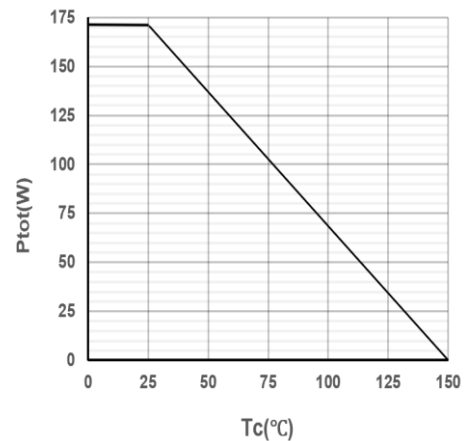
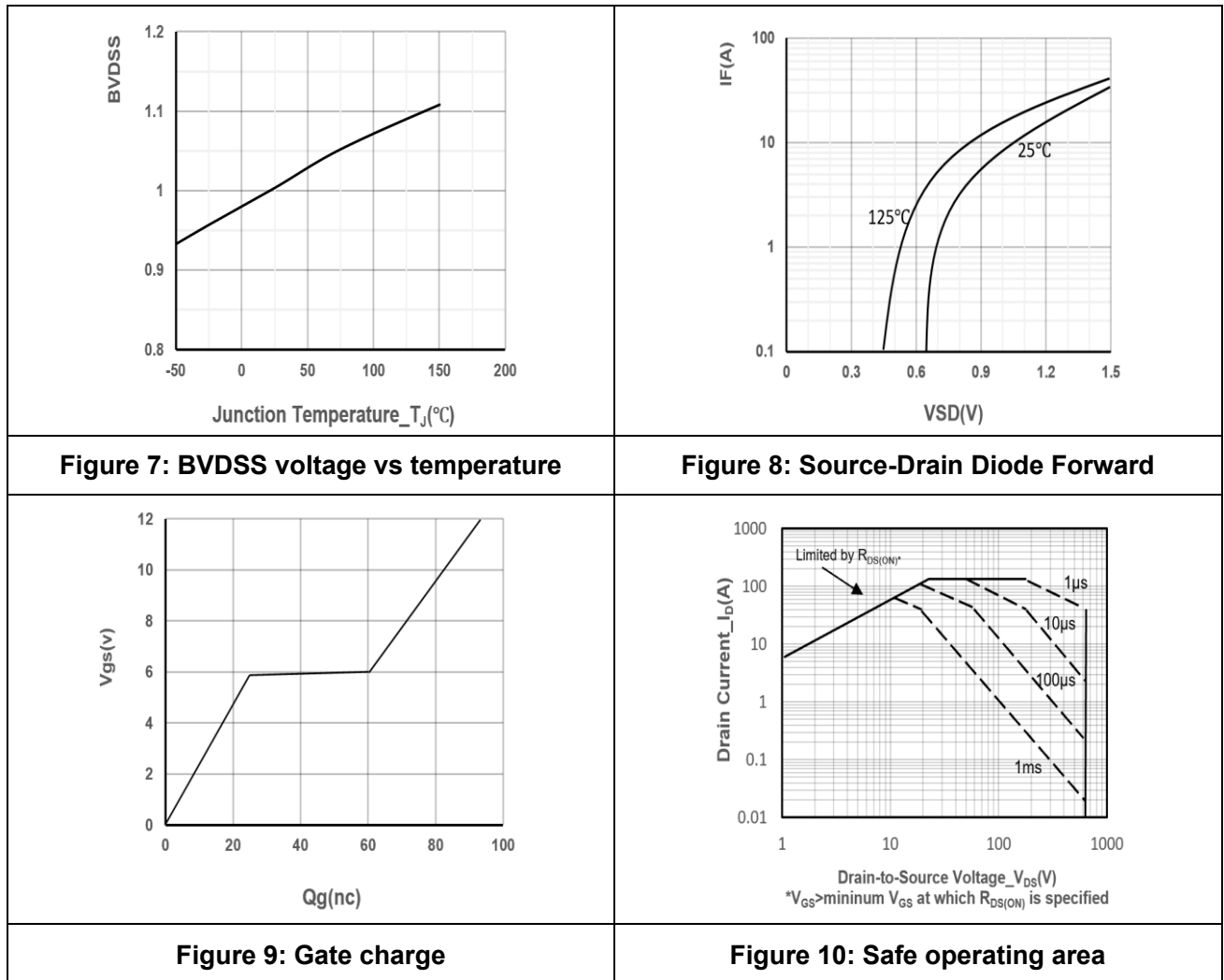


Figure 6: Power Dissipation

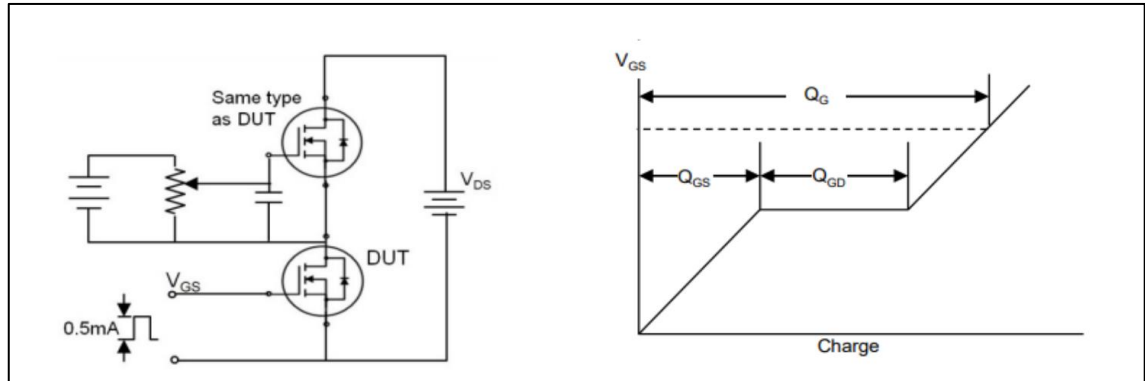


➤ Typical Performance Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

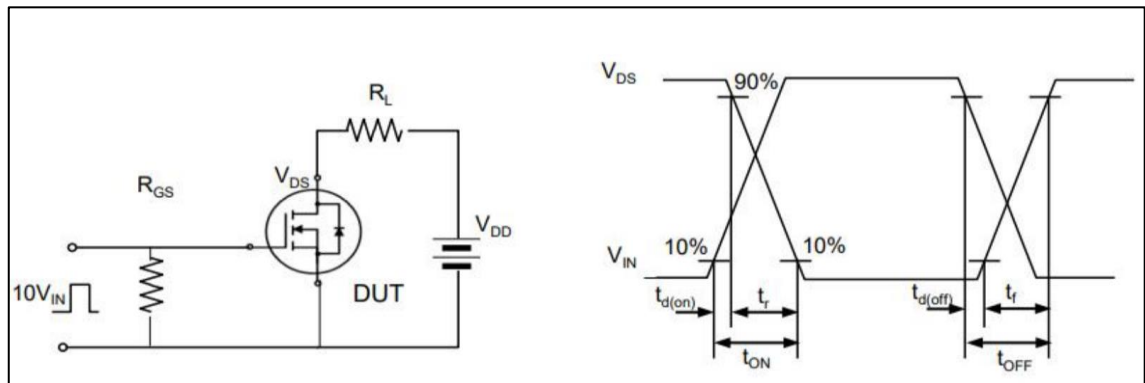


## ➤ Test Circuits

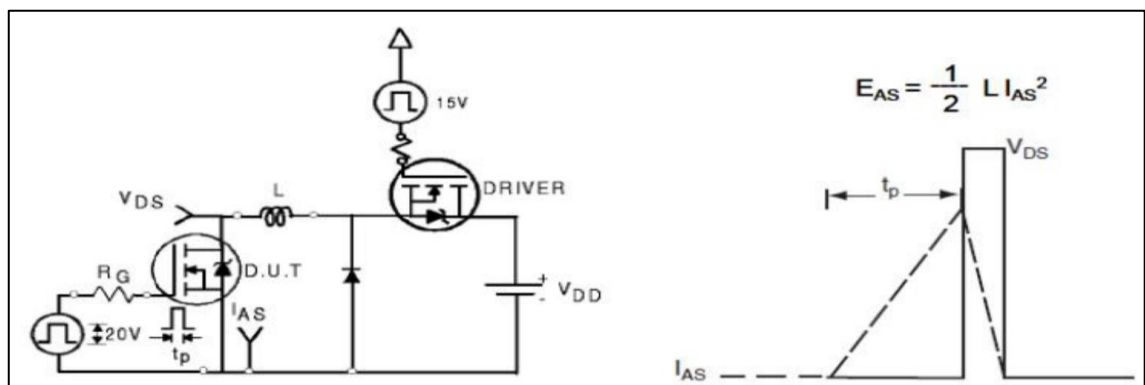
### 1. Gate charge test circuit & waveform



### 2. Switching time test circuit & waveform

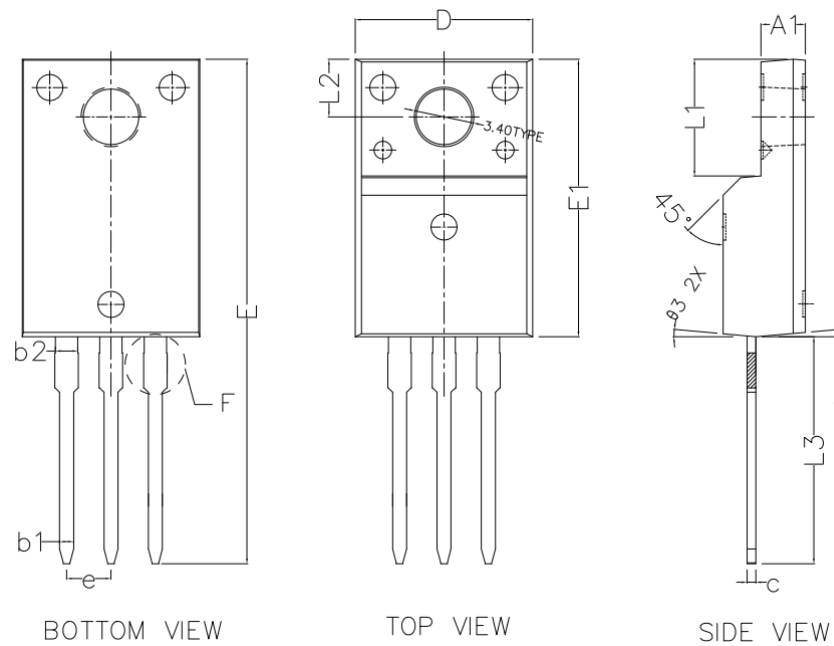


### 3. Unclamped Inductive switching test circuit & waveform



## ➤ Package Information

TO220F-3L



| COMMON DIMENSIONS<br>(UNITS OF MEASURE IS mm) |          |        |        |
|---|----------|--------|--------|
|   | MIN      | NORMAL | MAX    |
| A1  | 2.440    | 2.540  | 2.640  |
| A2  | 4.600    | 4.700  | 4.800  |
| A3  | 2.730    | 2.830  | 2.930  |
| b1  | 0.750    | 0.800  | 0.850  |
| b2  | 1.230    | 1.280  | 1.330  |
| c   | 0.450    | 0.500  | 0.550  |
| D   | 10.060   | 10.160 | 10.260 |
| E   | 28.650   | 28.850 | 29.050 |
| E1  | 15.770   | 15.870 | 15.970 |
| e   | 2.54TYPE |        |        |
| L1  | 6.68REF  |        |        |
| L2  | 3.30REF  |        |        |
| L3  | 12.830   | 12.980 | 13.130 |
| θ1  | 5° TYPE  |        |        |
| θ2  | 5° TYPE  |        |        |
| θ3  | 5° TYPE  |        |        |
| θ4  | 5° TYPE  |        |        |



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